

## **Probe Diagnostics of Confined Plasma Produced by 13.56 MHz R.F Plasma Source**

**M. KHORASSANI**

*Visiting Fellow. Physics dept. University of Shahid Beheshti .  
Tehran . Iran*

*Plasma Research Laboratory , Research School of Physical Science.  
The Australian National University .Canberra, ACT. 2601. Australia*

### **Abstract**

In an inductively coupled R.F plasma reactor, the plasma density increases smoothly for low increase of input power, but exhibits discontinuities or jumps. Variation of plasma temperature and density has been studied by using both single and double Langmuir probes. Other measurements showed that there is smooth increase in the plasma density, by increasing magnetic coil current and the R.F power.

Measurements have also confirmed earlier observations that the higher R.F power strongly depends on, to the higher chamber pressure and plasma potential.

**Keywords:** *Probe Diagnostics, Confined Plasma, R.F Plasma Source*

### **Introduction:**

Ion bombardment during the etching process has been found to be very important in the control of the profiles of the features, etched in silicon and polycrystalline silicon (Suzuki *et al.*, 1985). The ion flux incident on the surface is controlled by the density of the plasma. In the etching of very small device feature in thin semiconductor layers, it is therefore important to be able to control independently the plasma density and the energy of the plasma species bombarding the substrate (Boswell *et al.*, 1989). In conventional parallel-plate etching reactors any attempt to increase the plasma density by increasing the input power to the system, will result an

increase in the plasma potential (Boswell *et al.*, 1989) since this parameter is determined by the peak voltage appearing on the driven electrode (Vella *et al.*, 1985).

However, control over the plasma parameter can be achieved by using an inductively coupled R.F plasma as described by (Chen F.F. *et al.*, 1985). In this system the plasma is produced by coupling R.F power at 13.56 MHz through a two matching network to helicon antenna wound around the source. Experiments has shown that this type of reactor can be operated so that the plasma density and the plasma potential are virtually independent of each other (Haddelstone *et al.*, 1965). In this report we will present results of study of the transition to this mode of operation, and a large body of data was recorded using a computer controlled Langmuir probes.

**Experimental Apparatus**

The apparatus used in this experiment is shown schematically in Figure 1. It consists of a cylindrical aluminum vacuum chamber 25 cm in diameter, and 25 cm in length connected to the R.F source.

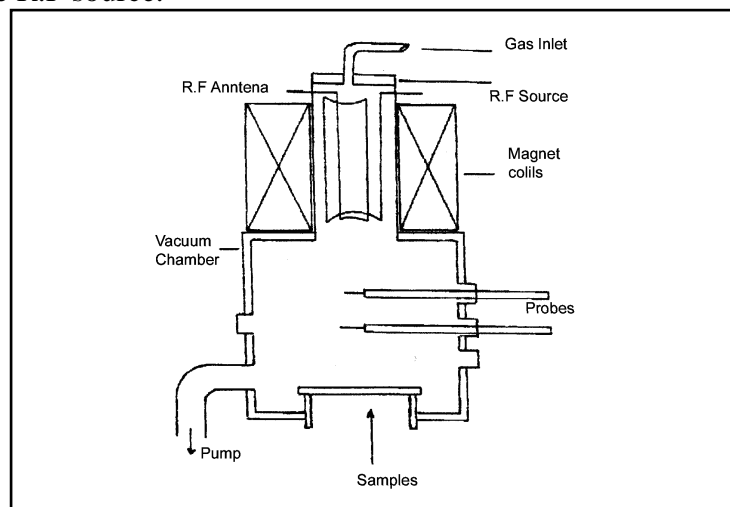


Figure 1- Schematic diagram of vacuum system with R.F source.



Where,  $I_+$  is the random ion current in amperes,  $A_p$  the area of probe in  $m^2$ ,  $m_+$  the ion mass  $1.67 \times 10^{-27}$  kg per photon,  $n_+$  the ion density  $No/m^3$  and  $V = \left[ \frac{2KT}{m_+} \right]^{\frac{1}{2}}$  is mean kinetic ion velocity m/sec. This expression holds only when  $T_e < T_i$ . If this situation does not obtain, the ions arrive at the probe with a velocity that corresponds to approximately  $\frac{1}{2} KT_e$ . When  $T_e \ll T_i$  the saturation ion current is modified as:

$$I_+ = 0.4 A n_+ + ev_{th}$$

Thus, if the thermal speed of the electron is known, the plasma density can be found from the saturation current, or can be calculated from the electron temperature, which is found by inspecting the slop of the volt-ampere characteristics ( Frank *et al.*, 1972). As the probe potential is increased with respect to the plasma, the surface will start to receive more and more electrons, first the fast electrons, and then slower ones. As the result, when the positive current to the probe is reduced, the current vanishes as the electron and ion flows to the probe are equal. Thus with a negative current to the probe, the electron current is determined from the following relation (Padgarni,1972):

$$I_+ = \frac{1}{4} env_e Se^{-\frac{ev}{kt}}$$

Where:

$$v_e = \sqrt{\frac{8KT_e}{m_e}}$$

By analyzing the above equation, we find:

$$\ln(I_e) = \ln\left[\frac{1}{4}env_e s\right] - \frac{ev}{kt}$$

Consequently the tangent to the probe characteristics and a semi logarithmic plot is  $e/kt$ , which allows us to determine the electron temperature and the ion density. In a magnetic field



to the change of antenna power and density, causing electron ion recombination inside the running plasma.

Figure 7 exhibits the density versus the R.F power. This figure shows that at low power nearly the density remains constant, but at power of 200-300 watts it increases rapidly. These changes reach a maximum up to few times more than previous values at higher coil current. These variations seem to be due to magnetic field with high electron density which draws more and more power from the source.

An attempt was made to measure the axial profile of plasma characteristics. Therefore in these investigations the single probe position was changed in a line perpendicular to the source axis at 2cm intervals. Figure 8, shows the radial variation of temperature and density with probe positions. It can be seen that the plasma had a higher temperature around the axis. Also the plasma density decreases more steadily at both sides of the source axis. Further experiments showed that at very high pressure the plasma fluctuates, so that further from the axis the plasma density is low and unstable around the axis.

#### **DISCUSSION:**

The plasma characteristics have been measured over a large range of each of the external parameters. This has allowed the plasma behavior to be studied, and has provided an accurate basis for chasing the modes of operation. However we have demonstrated that a high density diffusion plasma can be created at certain conditions. At pressure below 2 m Torr and source power of 400- 700 watts a uniform plasma over at least 15 cm in diameter can be formed by a confined magnetic field.

The plasma density and temperature determined in this work can be changed by varying the R.F power. Thus the R.F coupling technique employed in etching of thin film purposes, can be improved.



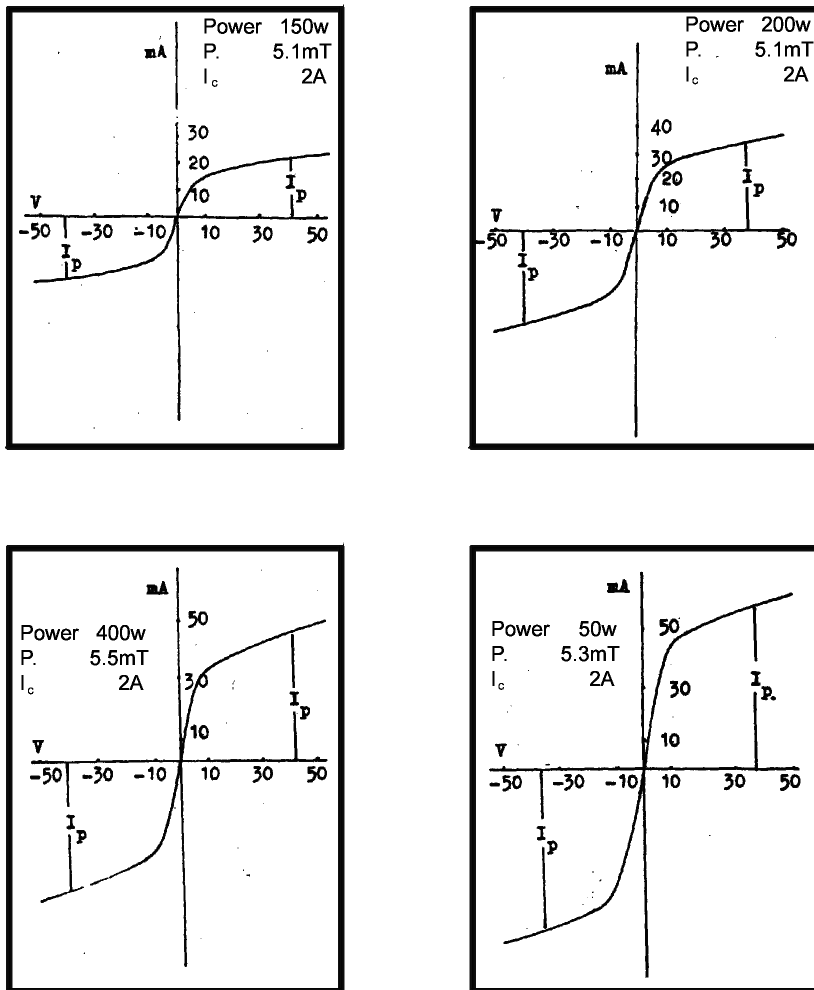


Figure 3 – Double Langmuir probe characteristics around the source axis.





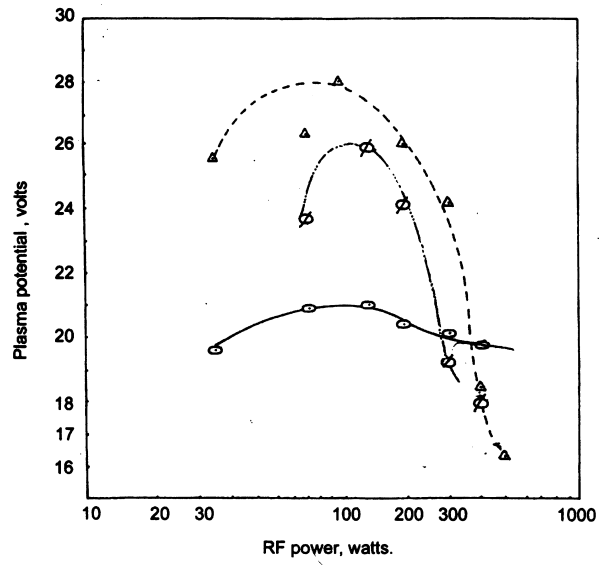


Fig. 6 - Variation of RF power with plasma potential at 3A ( $\Delta$ ), 1.5A ( $\odot$ ) and ( $\ominus$ ) magnetic coil current.

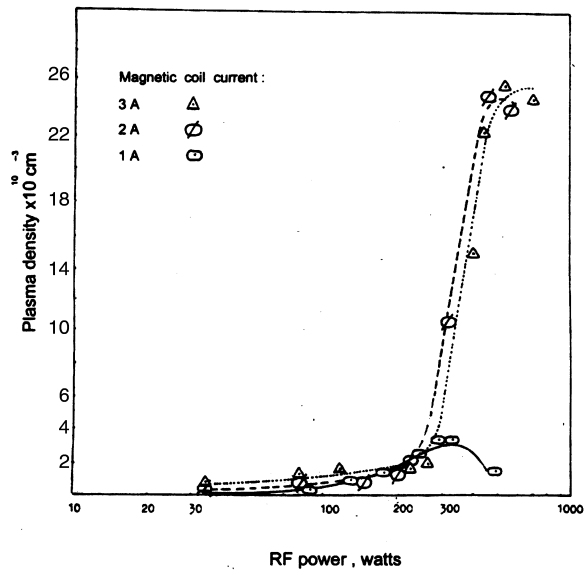


Fig. 7 Variation of plasma density with RF power at  $3.5 \times 10^{-3}$  torr pressure

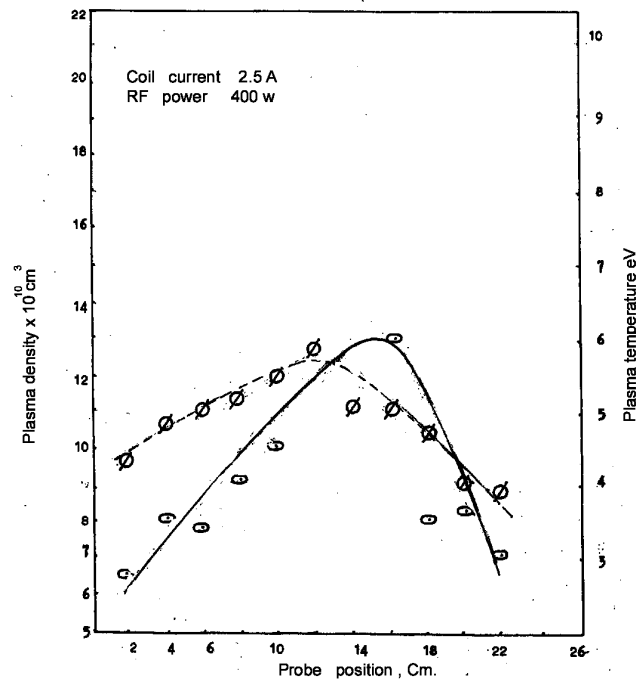


Figure 8 – Radial profile of probe position with plasma density ( $\emptyset$ ) and plasma temperature ( $\text{?}\bar{A}$ ).

**References:**

Suzuki, K., Ninomiya, K., and Nishimatsu, S., (1985). *Radio frequency based microwave plasma etching techniques. A method to increase  $\text{sio}_2$  etch rate.* J.Vac, Sci. technol **B3** (4), 1025-1034.

Boswell, R.W., and Porteous, R.K., (1987) *Etching in pulsed plasma.* J. Appl. Phys. **62**(8),3123-3129.

Boswell R.W., Morey, I.J., and Porteous,R.K., (1989), *Wave phenomena preceding during a beam plasma discharge.* J.of Geophysical research. **94**(3), 2654-2665.

- Boswell R.W, and Perry A.J., (1989) *Large Volume high density R.F inductively coupled plasma*, Appl. Phys. Lett. **50**(17),1130-1132.
- Vella M.C., and Lambert, A.J.D., (1985) *Development of R.F plasma generators for neutral beams*. J.Vac. Sci. Technol, **A3**(3), 147-158.
- Chen, F.F., (1986) *Measurement of low plasma densities in a magnetic field*, The Physics of fluid, **11**(4),811-820.
- Haddelstone, R.A., and Leonard, S.L., (1965) *Plasma diagnostics technique*, Academic press Newyork , p: 374-383.
- Frank, D.A., and Kamenetskii, A., (1972) *Plasma the fourth state of matter*, Plenum press , Newyork, chap 1, p:11-18.
- Padgorni,I.M., (1971) *Topics in plasma diagnostics*. Plenum Press, Newyork, p:10-22.